

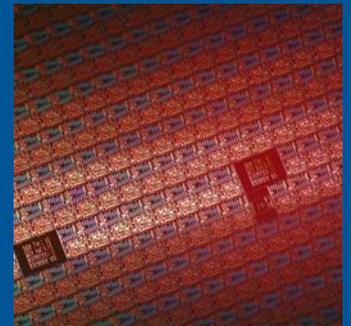


Accelerating the next technology revolution

# 2014 EUVL Symposium *Closing Address*

*Stefan Wurm, SEMATECH*  
*Patrick Naulleau, LBNL*

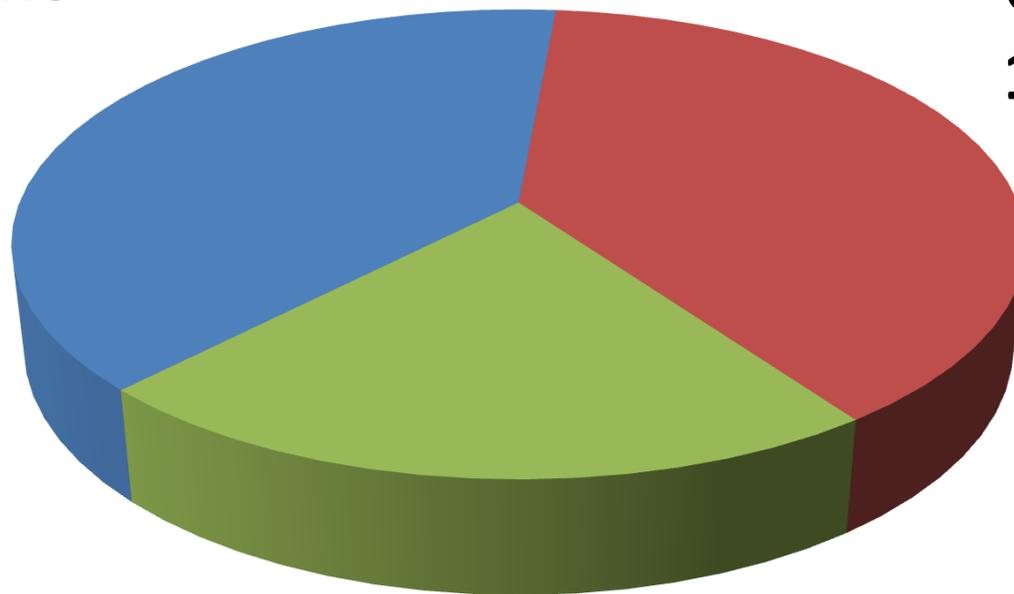
October, 29 2014



# EUVL Symposium Attendance in 2014: By Geographic Region

**Asia / Pacific**  
**105 (39%)**

**United States**  
**104 (39%)**

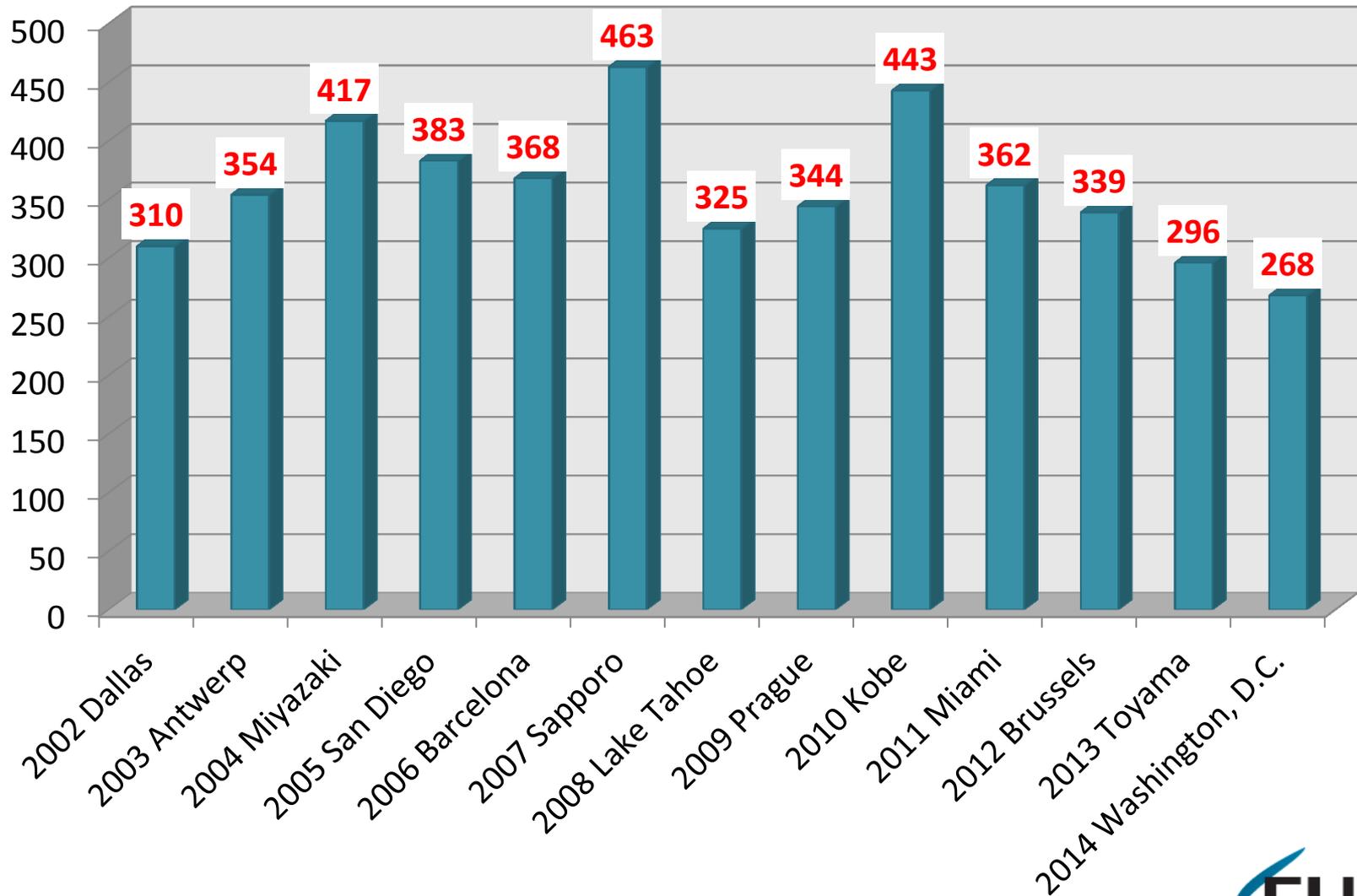


**Europe**  
**59 (22%)**

**268 Participants**



# EUVL Symposium Attendance by Year





# Some Highlights

# General Observations

- Overall, tone and outlook at the conference is positive: we are not out of the woods yet but we are on the right path (Tony Yen, TSMC)
- However, EUVL is under pressure to make significant progress over the next 12 months to become the irreversible (or reversible) 7 nm litho choice for leading edge foundry customers
- Anamorphic Lithography for high NA EUV – a major breakthrough for EUV Extendibility
  - Until recently it looked as if EUV would run out of nodes with 7 nm being seen as the last node where EUVL could be used in SP
  - The Anamorphic Lithography approach re-establishes EUVL as a multi-node technology

# EUV Source

- 80W source power demonstrated in the field
  - Very encouraging that we do meet roadmap milestones as planned
  - Must meet 125W in 1H 2015
- Two customers demonstrate > 500 wafers/day on NXE3300

# EUV Mask

- Actinic mask metrology tools (blank inspection and mask review) are coming online
  - Actinic patterned mask inspection remains an open challenge
- Mask blank defect reduction was demonstrated
  - Need to see this now at yield coming from commercial supply chain
  - Mask blank material supply could quickly become a bottle neck
- Pellicle membrane technology makes good progress but an industry integrated business strategy needs to be implemented

# EUV Resist

- The general perception is that progress in resist materials improvement has stalled
  - There was little substantial progress over the last year
  - If not addressed, resist material readiness is at risk of quickly becoming a bottle neck for EUVL introduction
- A lot of excellent non-CAR materials research work is happening
  - This needs to quickly translate into supplier development of those new materials to drive them towards meeting manufacturing requirements



# EUV Focus Areas

# EUVL Focus Areas 2009-2013:

## 22 nm half-pitch insertion target



2009 / 22hp	2010 / 22hp	2011 / 22hp	2012 / 22hp	2013 / 22hp
1. Mask yield & defect inspection/review infrastructure	1. Mask yield & defect inspection/review infrastructure	1. Long-term reliable source operation with 200 W at IF*	1. Long-term reliable source operation with a. 200 W at IF in 2014 b. 500 W-1,000 W in 2016	1. Long-term reliable source operation with a. 125 W at IF in 2014 b. 250 W in 2015
2. Long-term reliable source operation with 200 W at IF	1. Long-term reliable source operation with 200 W at IF	2. Mask yield & defect inspection/review infrastructure	2. Mask yield & defect inspection/review infrastructure	2. Mask yield & defect inspection/review infrastructure
3. Resist resolution, sensitivity & LER met simultaneously	2. Resist resolution, sensitivity & LER met simultaneously	3. Resist resolution, sensitivity & LER met simultaneously	3. Resist resolution, sensitivity & LER met simultaneously	4. Keeping mask defect free – Availability of pellicle mtg HVM req't – Minimize defect adders during use
• EUVL manufacturing integration	4. Resist resolution, sensitivity & LER met simultaneously			

Ranked by 12<sup>th</sup> International EUVL Symposium Program Steering Committee. Toyama, Japan October 10, 2013

## From 2013 Symposium



# 2014 EUVL Focus Areas



Key Focus Areas	Rank*	StdDev
<b>Reliable source operation with &gt; 75% availability</b> - 125 W at IF in 1H / 2015 (at customer) - 250 W at IF in 1H / 2016 (HVM entry at customer)	1.2	0.48
<b>Resist resolution, sensitivity &amp; LER met simultaneously</b> - Progress insufficient to meet 2015 introduction target	2.3	0.78
<b>Mask yield &amp; defect inspection/review infrastructure</b> - Enable high yield defect free mask blank supply chain	3.1	1.08
<b>Keeping mask defect free</b> - Availability of pellicle meeting HVM requirement – need integrated industry strategy for solution - Minimize defect adders during use	3.3	0.89

*Ranked by 13<sup>th</sup> International EUVL Symposium Program Steering Committee. Washington, D.C., October 29, 2014*



*\*) Average of steering committee member votes*

# EUVL Focus Areas 2012-2014



2012 / 22hp	2013 / 22hp	2014 / 16hp
<p>1. Long-term reliable source operation with</p> <ul style="list-style-type: none"> <li>a. 200 W at IF in 2014</li> <li>b. 500 W-1,000 W in 2016</li> </ul>	<p>1. Long-term reliable source operation with</p> <ul style="list-style-type: none"> <li>a. 125 W at IF in 2014</li> <li>b. 250 W in 2015</li> </ul>	<p>1. Reliable source operation with &gt; 75% availability</p> <ul style="list-style-type: none"> <li>– 125 W at IF in 1H / 2015 (at customer))</li> <li>– 250 W at IF in 1H / 2016 (HVM entry at customer)</li> </ul>
<p>2. Mask yield &amp; defect inspection/review infrastructure</p>	<p>2. Mask yield &amp; defect inspection/review infrastructure</p>	<p>2. Resist resolution, sensitivity &amp; LER met simultaneously</p> <ul style="list-style-type: none"> <li>– Progress insufficient to meet 2015 introduction target</li> </ul>
<p>3. Resist resolution, sensitivity &amp; LER met simultaneously</p>	<p>4. Keeping mask defect free</p> <ul style="list-style-type: none"> <li>– Availability of pellicle mtg HVM req't</li> <li>– Minimize defect adders during use</li> </ul>	<p>3. Mask yield &amp; defect inspection/review infrastructure</p> <ul style="list-style-type: none"> <li>– Enable high yield defect free mask blank supply chain</li> </ul>
<ul style="list-style-type: none"> <li>• EUVL manufacturing integration</li> </ul>	<p>4. Resist resolution, sensitivity &amp; LER met simultaneously</p>	<p>3. Keeping mask defect free</p> <ul style="list-style-type: none"> <li>– Availability of pellicle mtg HVM req't : need integrated industry strategy for solution</li> <li>– Minimize defect adders during use</li> </ul>

*Ranked by 13<sup>th</sup> International EUVL Symposium Program Steering Committee, Washington, D.C. October 29, 2014*





# 2015 EUVL Symposium Announcement

K. Ronse, E. Hendrickx



ANNOUNCEMENT 1

**EUV SYMPOSIUM 2015**

K. RONSE, E. HENDRICKX

ANNOUNCEMENT 1

29 OCTOBER 2014



# FOCUS POINTS EUVS 2015

## ▶ Day 1 :

### **EUUV readiness :**

- Will EUVL meet the N7 insertion deadline ?  
(invited speakers, NXE:3300 users)

## ▶ Day 2-3 :

### **EUUV extendibility :**

- Progress on EUV (alternative) resist materials
- Progress EUV alternative mask architectures
- Progress EUV pellicles and implementation
- Progress EUV reticle inspection
- Progress EUV high power sources
- Progress high NA EUV anamorphic

# DATE AND ORGANIZATION

The next EUVL symposium will be held in Europe :

**week of 4-7 October 2015**

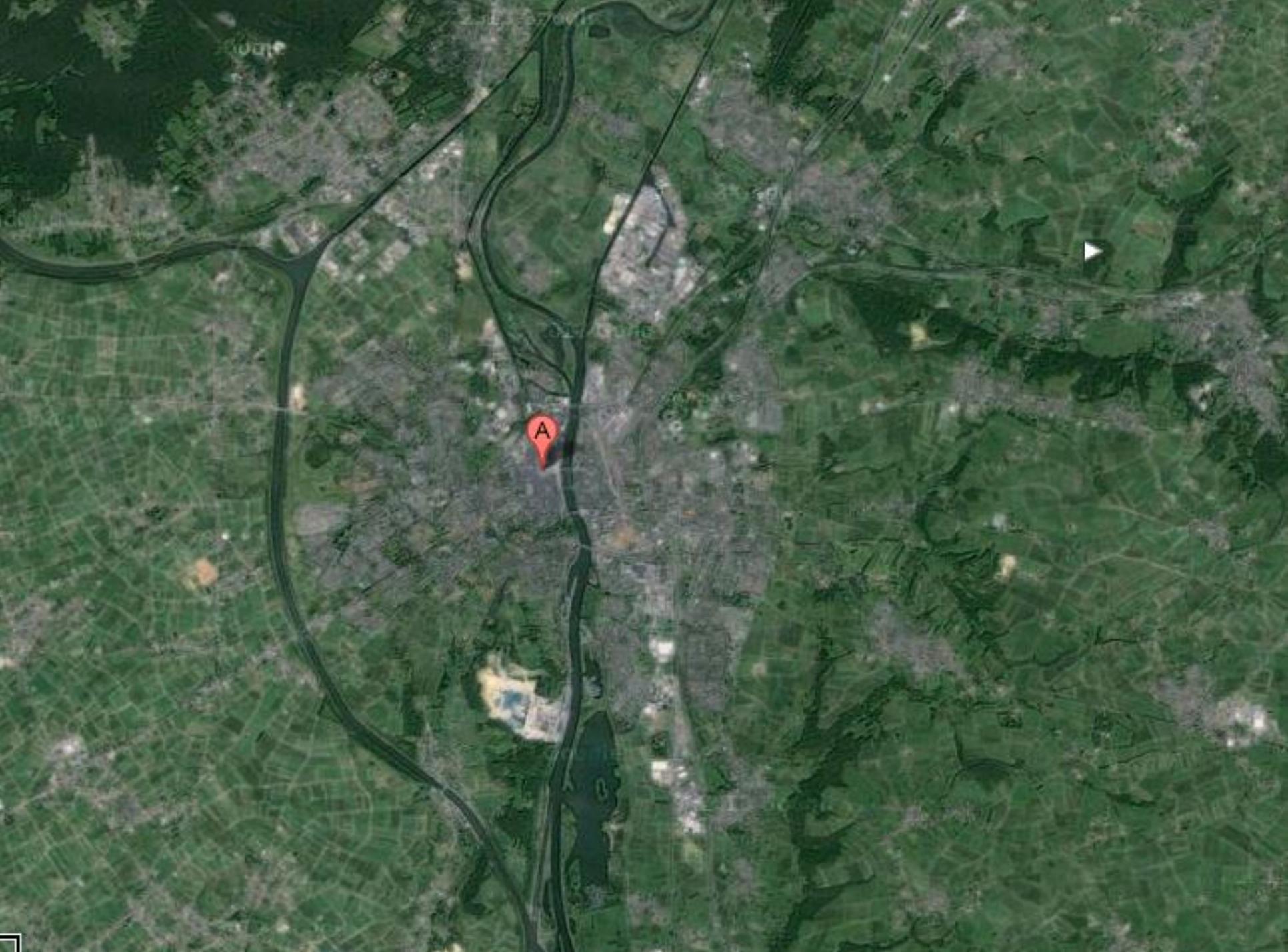
organized by imec, in cooperation with SEMATECH and EIDEC

Symposium Chair : Kurt Ronse

Program Chair : Eric Hendrickx

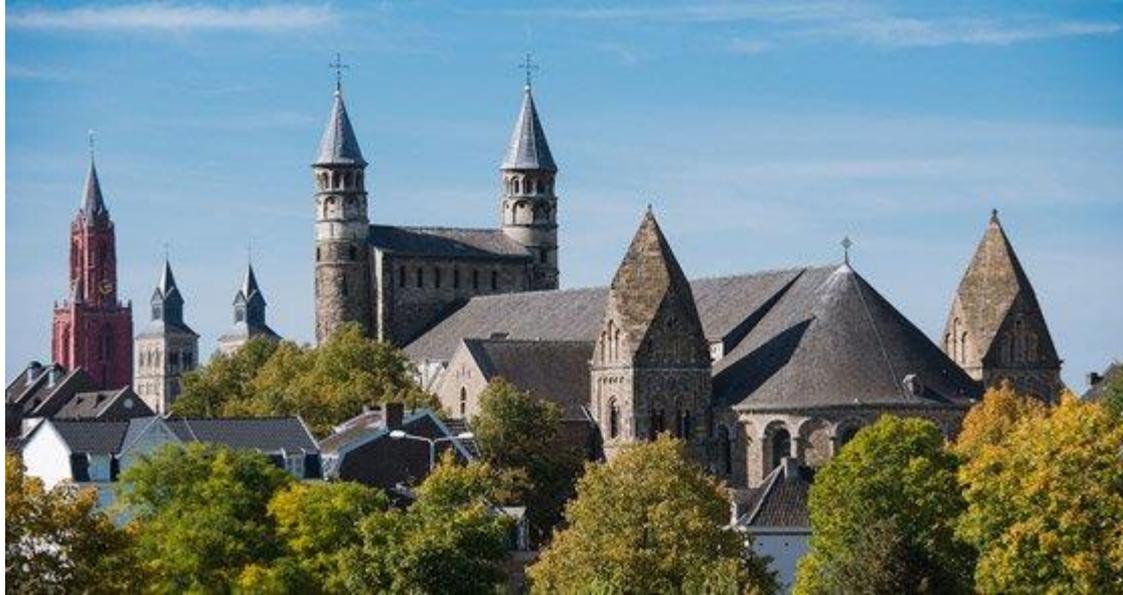






# LOCATION : MAASTRICHT (NL)









# MAASTRICHT



# MAASTRICHT

## HOW TO REACH ?

- ▶ 2 major airports at  $\approx 100$ km from Maastricht
  - Brussels International Airport (Belgium)
  - Dusseldorf International airport (Germany)
  
- ▶ Public transport from airport to MECC
  - Trains
  - Bus shuttle service (being considered)

# CONFERENCE CENTER MECC



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# ACCOMMODATION : NH MAASTRICHT HOTEL



87,00USD/night

- ▶ Free buses connect city center with MECC
- ▶ Other hotel options in city center

**MARK YOUR CALENDARS !!!**

**4-7 October 2015**

A large, abstract graphic of purple smoke or ink swirling and falling from the top left towards the center of the page.

**ASPIRE  
INVENT  
ACHIEVE**



imec



# Best Poster / Best Presentation

# International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.

2014 EUVL Symposium Best Poster Presentation

*Excellence Award*

Presented to

Antoine Wojdyla  
Berkeley Lab

*Fourier Ptychography Microscopy with SHARP EUV Microscope for Increased  
Imaging Resolution Based on Illumination Diversity*

# International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.

2014 EUVL Symposium Best Paper Presentation

*Excellence Award*

Presented to

**Sascha Migura**  
**Carl Zeiss SMT GmbH**

*EUV Lithography Optics for sub 9nm Resolution*

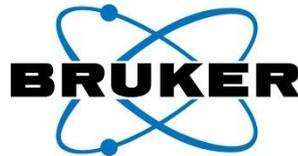


# Thank you & Symposium Dinner

# International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.

## 2014 EUVL Symposium Sponsors – Thank You!

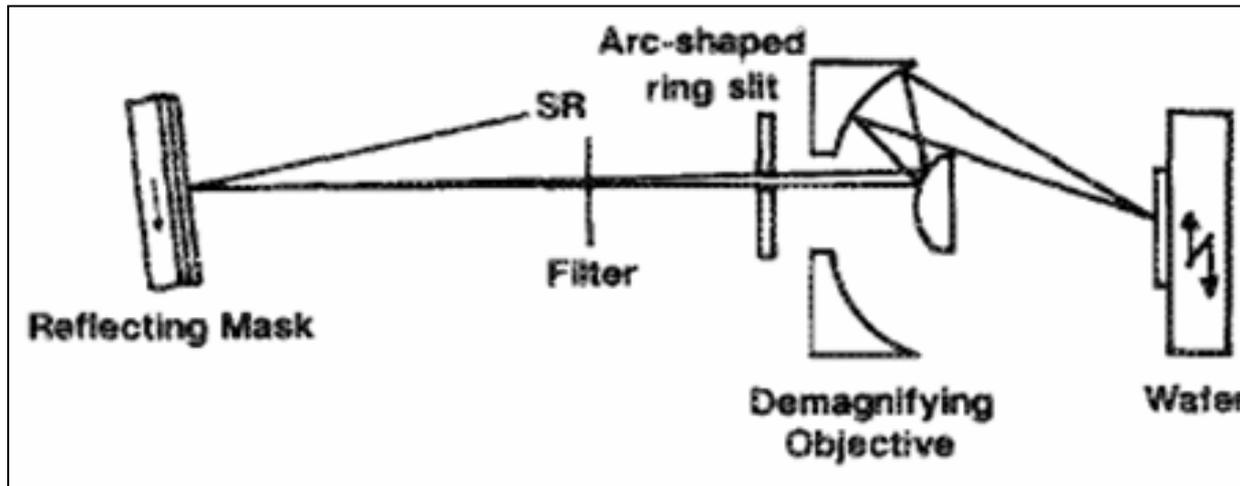


# Thank you!

- Symposium co-chairs:  
Toshiro Itani (EIDEC), Kurt Ronse (imec)
- Program co-committee:  
Patrick Naulleau  
Soichi Inoue (EIDEC), Winfried Kaiser (Carl Zeiss)  
All abstract reviewers
- Program logistics / support  
Marcy DeBiccary, Kelly Abbruzzese  
Our session chairs
- All paper / poster presenters  
With special thanks to our keynote and invited speakers

# Thank you to an EUVL Pioneer!

Prof. Dr. Hiroo Kinoshita



# Symposium Dinner

- Buses will leave at 6:30 PM
- Parkview Entrance of hotel
  - Lobby level, East Side
- Please have your name badge (if possible) to check-in prior to boarding the bus